WS4A010120A

Silicon Carbide Schottky Diode

G4 MPS Technology

V_{RRM}	=	1200	V
I_F (T_C 5)	=	14	A
Q_C	=	41	nC

Features

- New Thin Wafer Technology
- Low Forward Voltage Drop (V_F)
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on V_F
- Temperature-independent Switching

Package

Benefits

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

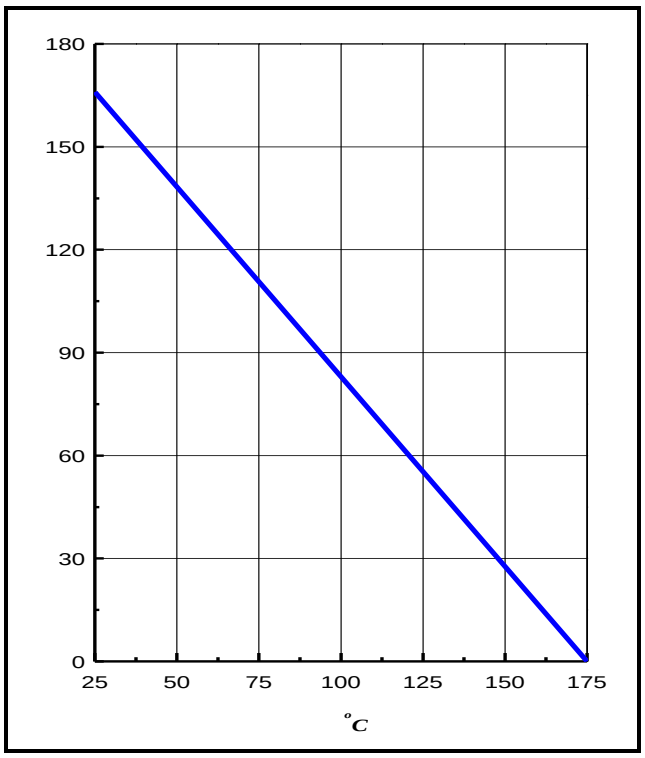
Applications

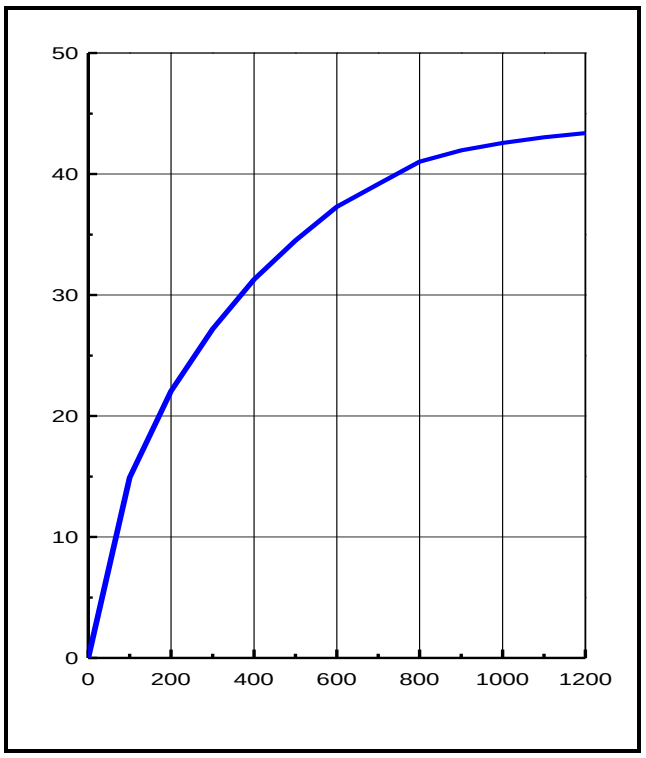
- Switch Mode Power Supplies
- Uninterruptible Power Supplies
- Motor drive, PV Inverter, Wind Power Station

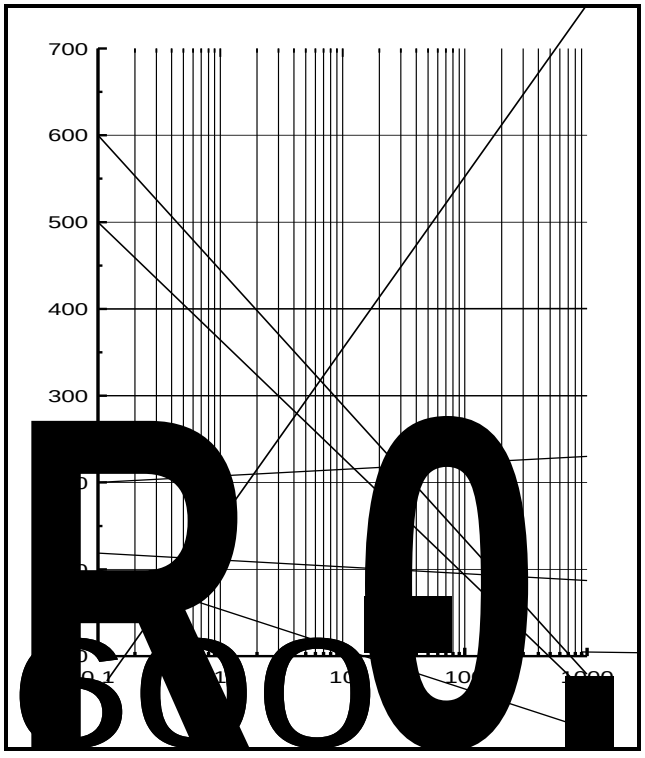
Part Number	Package	Marking
WS4A010120A	TO-220-2	WS4A010120A

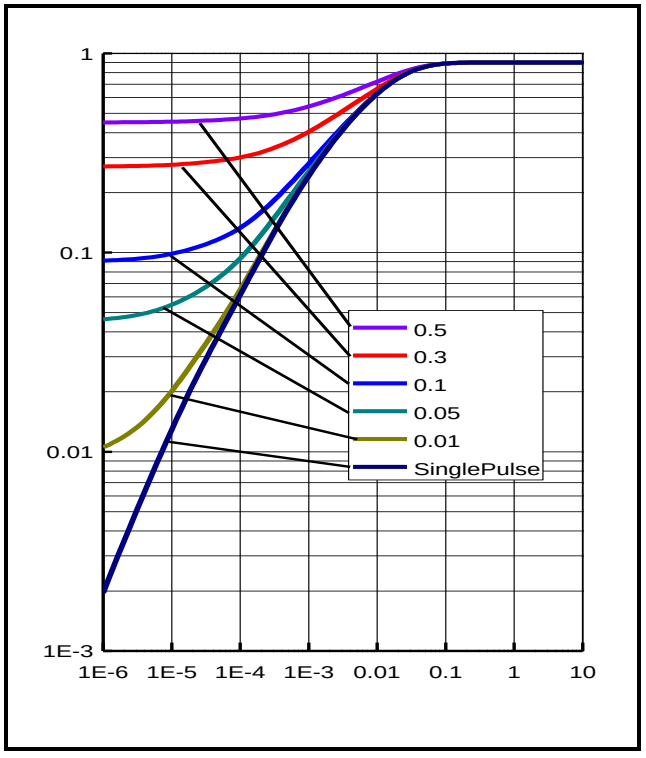
Electrical Characteristics F

Typical Performance



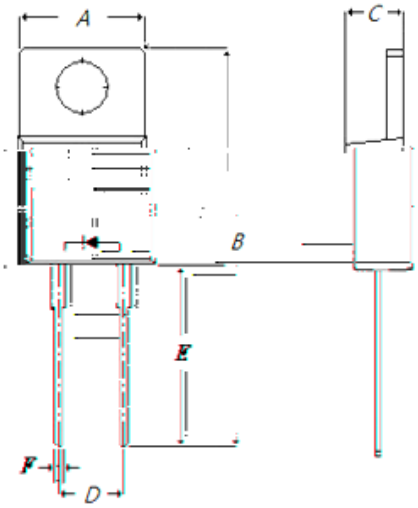






Package Dimensions

Package TO-220-2



mbol	Min. (mm)	Typ. (mm)	Max. (mm)
A	9.17	10.08	10.91